Is Now Part of

ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

May 2015

FDPC5030SG

PowerTrench® Power Clip
30V Asymmetric Dual N-Channel MOSFET

Features

Q1: N-Channel

- Max $r_{DS(on)}$ = 5.0 mΩ at V_{GS} = 10 V, I_D = 17 A
- Max $r_{DS(on)}$ = 6.5 mΩ at V_{GS} = 4.5 V, I_D = 14 A

Q2: N-Channel

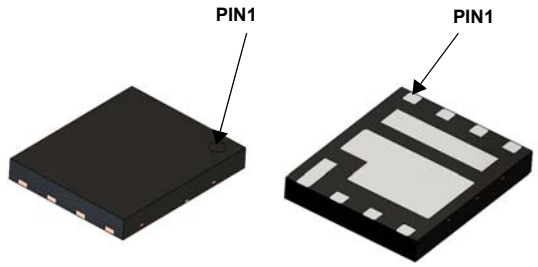
- Max $r_{DS(on)}$ = 2.4 mΩ at V_{GS} = 10 V, I_D = 25 A
- Max $r_{DS(on)}$ = 3.0 mΩ at V_{GS} = 4.5 V, I_D = 22 A
- Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses
- MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing
- RoHS Compliant

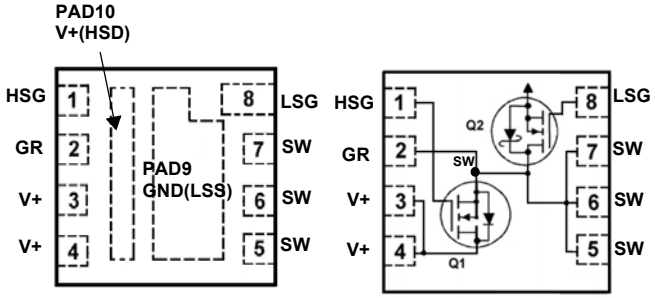
General Description

This device includes two specialized N-Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET™ (Q2) have been designed to provide optimal power efficiency.

Applications

- Computing
- Communications
- General Purpose Point of Load





Pin	Name	Description	Pin	Name	Description	Pin	Name	Description
1	HSG	High Side Gate	3,4,10	V+(HSD)	High Side Drain	8	LSG	Low Side Gate
2	GR	Gate Return	5,6,7	SW	Switching Node, Low Side Drain	9	GND(LSS)	Low Side Source

MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted.

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		30	30	V
V_{GS}	Gate to Source Voltage		±20	±12	V
I_D	Drain Current -Continuous	T_C = 25 °C (Note 5)	56	84	A
	-Continuous	T_C = 100 °C (Note 5)	35	53	
	-Continuous	T_A = 25 °C	17[Note1a]	25[Note1b]	
	-Pulsed	T_A = 25 °C (Note 4)	227	503	
E_{AS}	Single Pulse Avalanche Energy	(Note 3)	54	96	mJ
P_D	Power Dissipation for Single Operation	T_C = 25 °C	23	25	W
	Power Dissipation for Single Operation	T_A = 25 °C	2.1[Note1a]	2.3[Note1b]	
	Power Dissipation for Single Operation	T_A = 25 °C	1.0[Note1c]	1.1[Note1d]	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		-55 to +150		°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	5.6	4.9	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	60[Note1a]	55[Note1b]	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	130[Note1c]	120[Note1d]	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDPC5030SG	FDPC5030SG	Power Clip 56	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted.

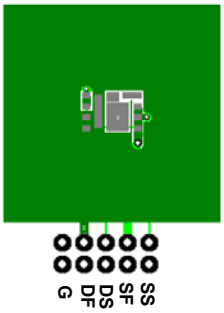
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Off Characteristics							
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V I_D = 1 mA, V_{GS} = 0 V	Q1 Q2	30 30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C I_D = 10 mA, referenced to 25 °C	Q1 Q2		15 16		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V V_{DS} = 24 V, V_{GS} = 0 V	Q1 Q2			1 500	μA μA
I_{GSS}	Gate to Source Leakage Current, Forward	V_{GS} = 20 V, V_{DS}= 0 V V_{GS} = 12 V, V_{DS}= 0 V	Q1 Q2			100 100	nA nA
On Characteristics							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA V_{GS} = V_{DS}, I_D = 1 mA	Q1 Q2	1.0 1.0	1.7 1.6	3.0 3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C I_D = 10 mA, referenced to 25 °C	Q1 Q2		-5 -3		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10V, I_D = 17 A V_{GS} = 4.5 V, I_D = 14 A V_{GS} = 10 V, I_D = 17 A,T_J =125 °C	Q1		4.1 5.4 5.7	5.0 6.5 7.0	mΩ
		V_{GS} = 10V, I_D = 25 A V_{GS} = 4.5 V, I_D = 22 A V_{GS} = 10 V, I_D = 25 A ,T_J =125 °C	Q2		1.9 2.4 2.7	2.4 3.0 3.4	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 17 A V_{DS} = 5 V, I_D = 25 A	Q1 Q2		93 139		S
Dynamic Characteristics							
C_{iss}	Input Capacitance	Q1: V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHZ Q2: V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHZ	Q1 Q2		1224 2730	1715 3825	pF
C_{oss}	Output Capacitance		Q1 Q2		397 801	560 1125	pF
C_{rss}	Reverse Transfer Capacitance		Q1 Q2		42 72	60 100	pF
R_g	Gate Resistance		Q1 Q2	0.1 0.1	0.5 1.1	1.5 2.2	Ω
Switching Characteristics							
$t_{d(on)}$	Turn-On Delay Time	Q1: V_{DD} = 15 V, I_D = 17 A, R_{GEN} = 6 Ω Q2: V_{DD} = 15 V, I_D = 25 A, R_{GEN} = 6 Ω	Q1 Q2		8 10	16 19	ns
t_r	Rise Time		Q1 Q2		2 4	10 10	ns
$t_{d(off)}$	Turn-Off Delay Time		Q1 Q2		18 30	33 48	ns
t_f	Fall Time		Q1 Q2		2 3	10 10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V Q1 V_{DD} = 15 V, I_D = 17 A Q2 V_{DD} = 15 V, I_D = 25 A	Q1 Q2		17 39	24 55	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V	Q1 Q2		8 18	11 26	nC
Q_{gs}	Gate to Source Gate Charge		Q1 Q2		3.1 6.1		nC
Q_{gd}	Gate to Drain “Miller” Charge		Q1 Q2		2.0 4.3		nC

Electrical Characteristics T_J = 25 °C unless otherwise noted.

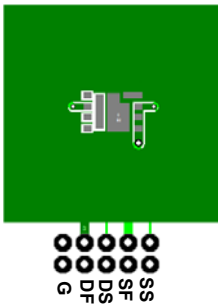
Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
Drain-Source Diode Characteristics							
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 17 A (Note 2) V_{GS} = 0 V, I_S = 25 A (Note 2)	Q1 Q2		0.8 0.8	1.2 1.2	V
t_{rr}	Reverse Recovery Time	Q1 I_F = 17 A, di/dt = 100 A/μs	Q1 Q2		23 27	37 44	ns
Q_{rr}	Reverse Recovery Charge	Q2 I_F = 25 A, di/dt = 230 A/μs	Q1 Q2		8 31	16 50	nC

Notes:

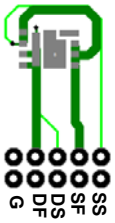
1.$R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material, $R_{\theta CA}$ is determined by the user's board design.



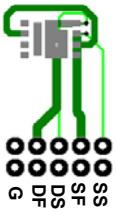
a. 60 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 55 °C/W when mounted on a 1 in^2 pad of 2 oz copper



c. 130 °C/W when mounted on a minimum pad of 2 oz copper



d. 120 °C/W when mounted on a minimum pad of 2 oz copper

2 Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

3. Q1 :E_{AS} of 54 mJ is based on starting T_J = 25 °C; L = 3 mH, I_{AS} = 6 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} =20 A.
Q2: E_{AS} of 96 mJ is based on starting T_J = 25 °C; L = 3 mH, I_{AS} = 8 A, V_{DD} = 30 V, V_{GS} = 10 V. 100% tested at L = 0.1 mH, I_{AS} =27 A.

4. Pulsed Id refer to Fig.11 and Fig.24 SOA curve for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted.

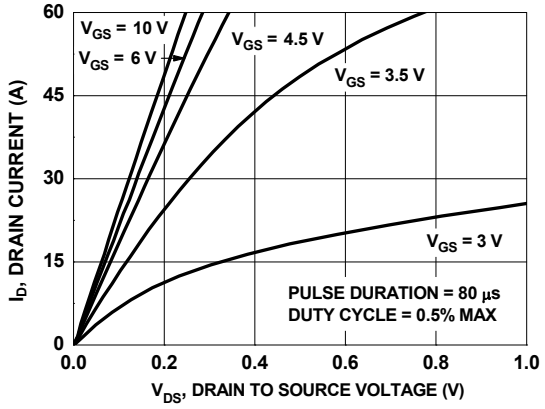


Figure 1. On Region Characteristics

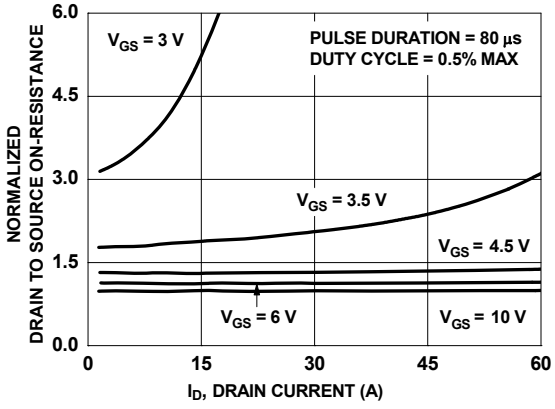


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

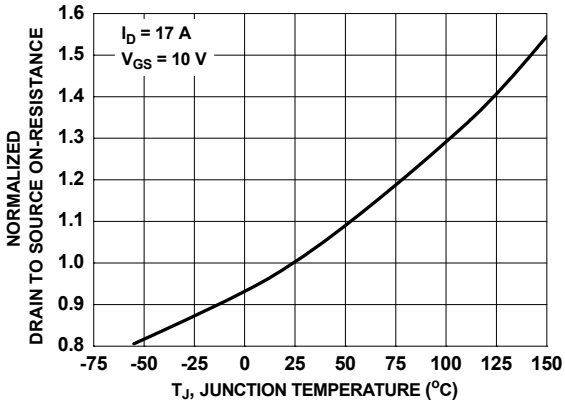


Figure 3. Normalized On Resistance vs. Junction Temperature

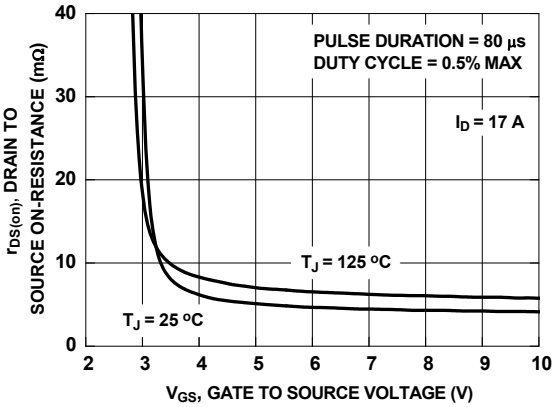


Figure 4. On-Resistance vs. Gate to Source Voltage

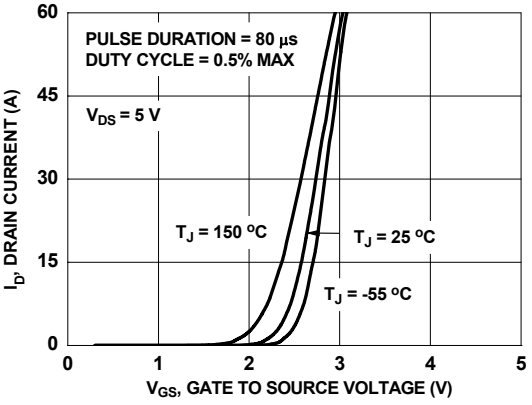


Figure 5. Transfer Characteristics

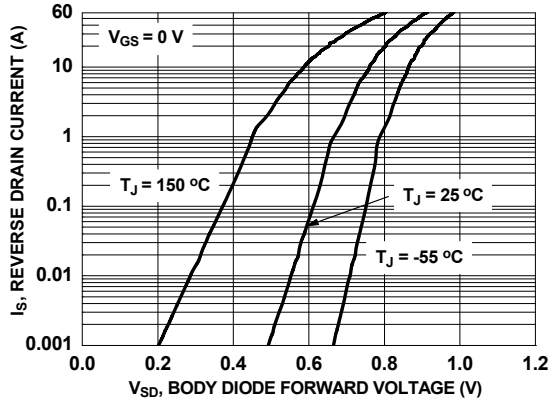


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted.

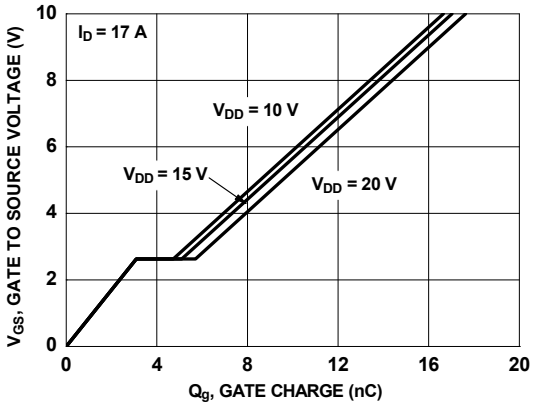


Figure 7. Gate Charge Characteristics

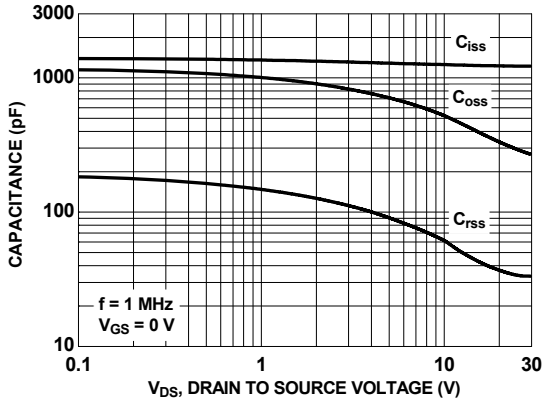


Figure 8. Capacitance vs. Drain to Source Voltage

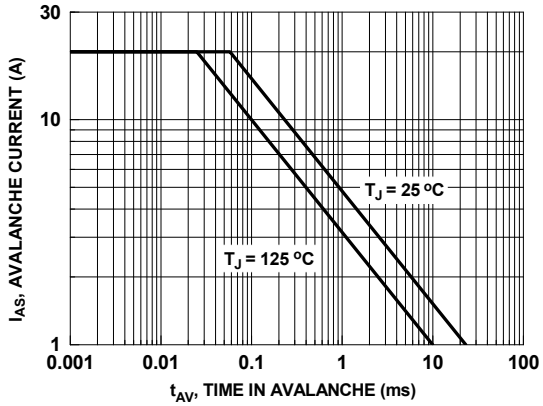


Figure 9. Unclamped Inductive Switching Capability

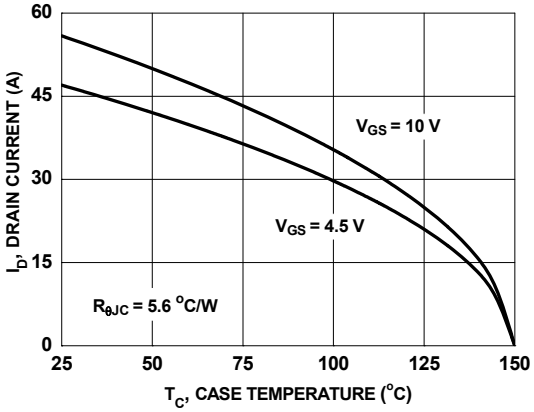


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

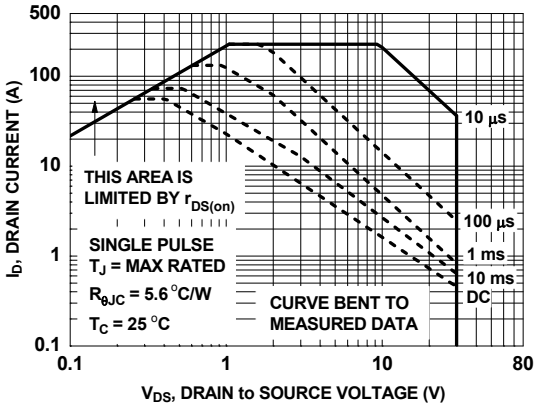


Figure 11. Forward Bias Safe Operating Area

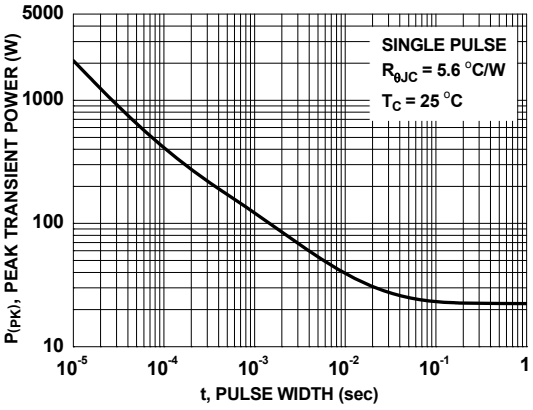


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q1 N-Channel) T_J = 25°C unless otherwise noted.

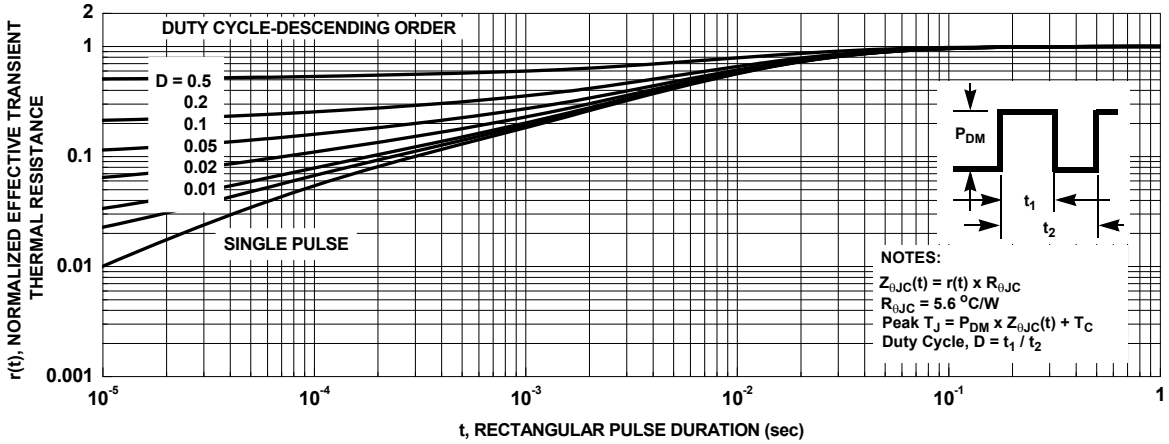


Figure 13. Junction-to-Case Transient Thermal Response Curve

Typical Characteristics (Q2 N-Channel) T_J = 25 °C unless otherwise noted.

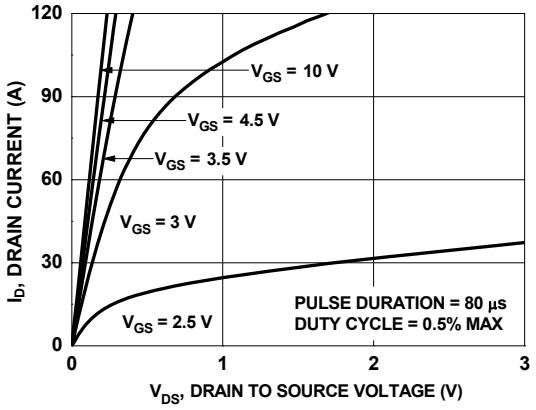


Figure 14. On- Region Characteristics

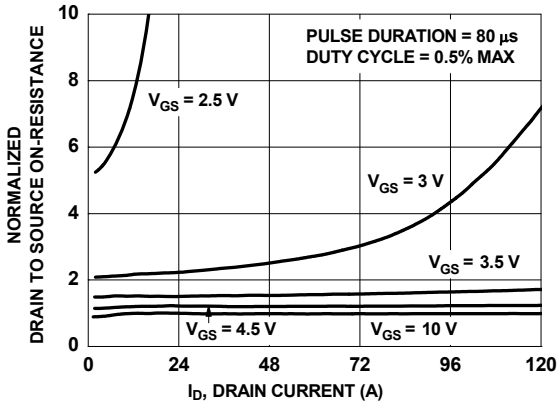


Figure 15. Normalized on-Resistance vs. Drain Current and Gate Voltage

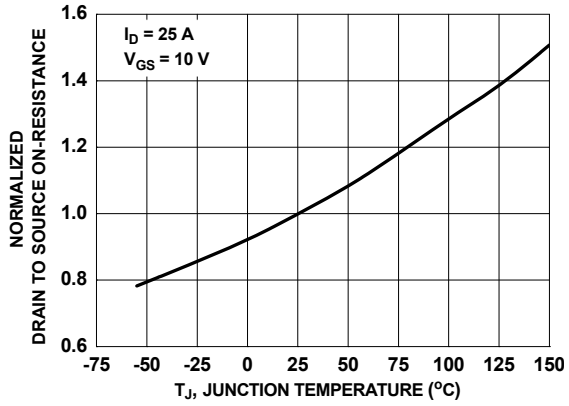


Figure 16. Normalized On-Resistance vs. Junction Temperature

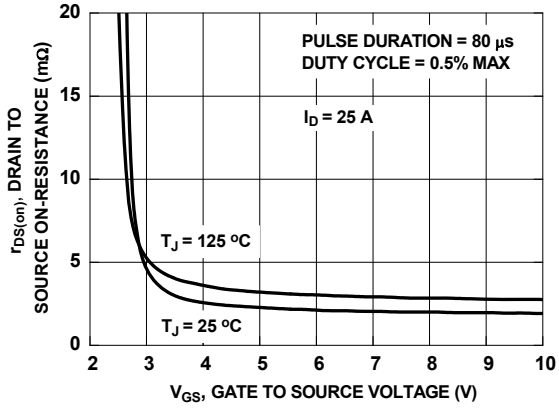


Figure 17. On-Resistance vs. Gate to Source Voltage

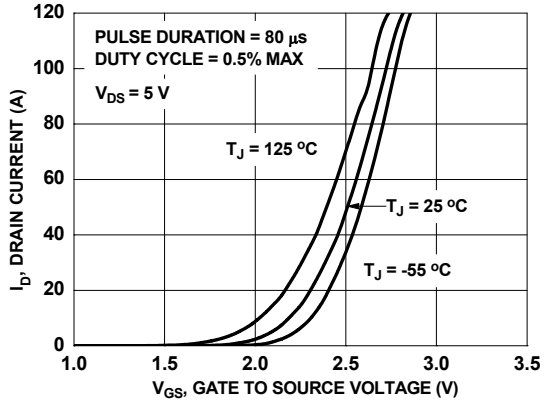


Figure 18. Transfer Characteristics

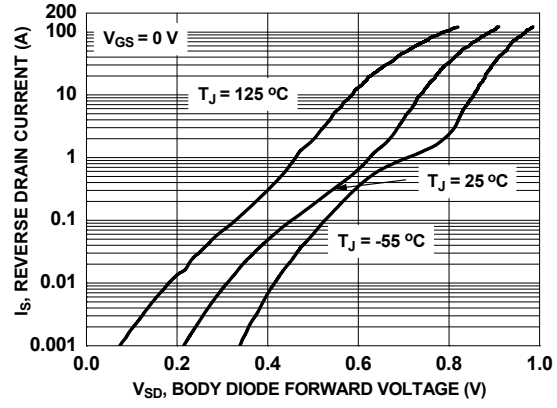


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics (Q2 N-Channel) T_J = 25°C unless otherwise noted.

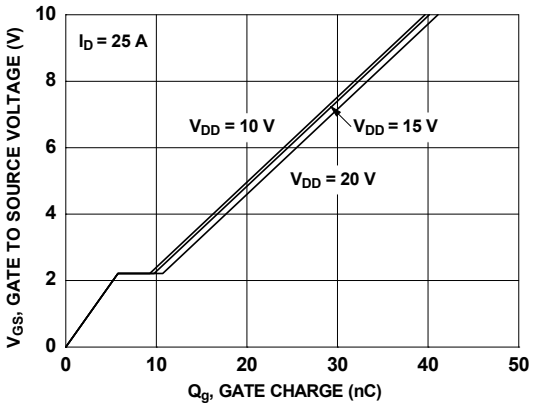


Figure 20. Gate Charge Characteristics

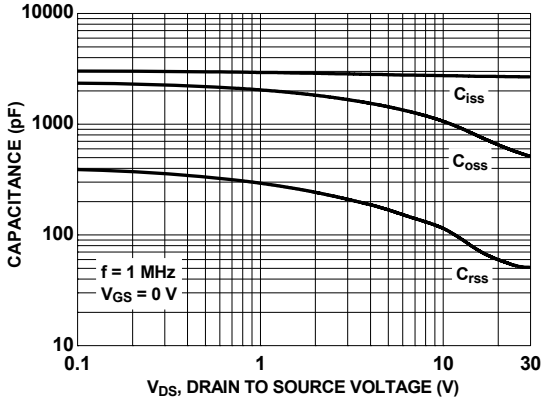


Figure 21. Capacitance vs. Drain to Source Voltage

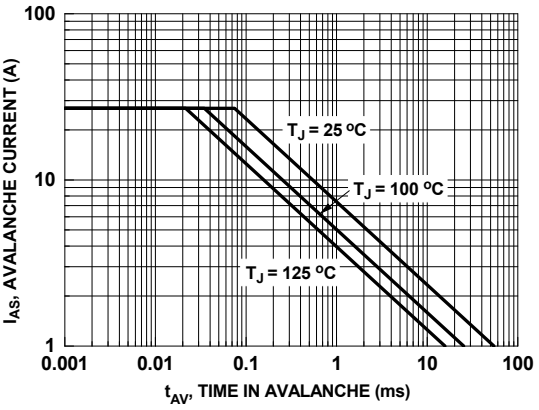


Figure 22. Unclamped Inductive Switching Capability

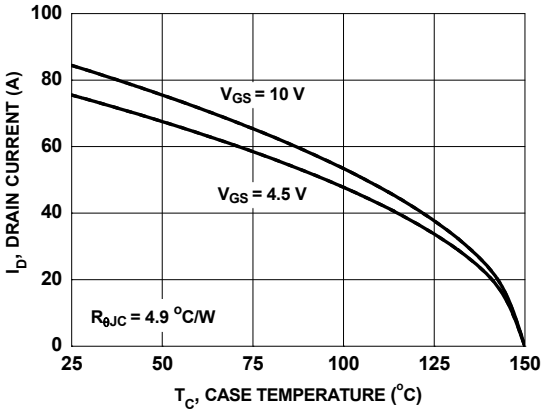


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

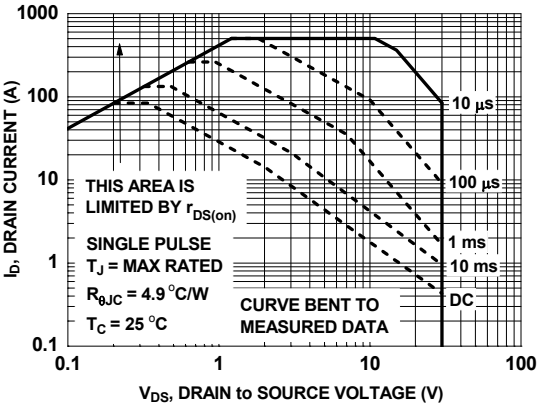


Figure 24. Forward Bias Safe Operating Area

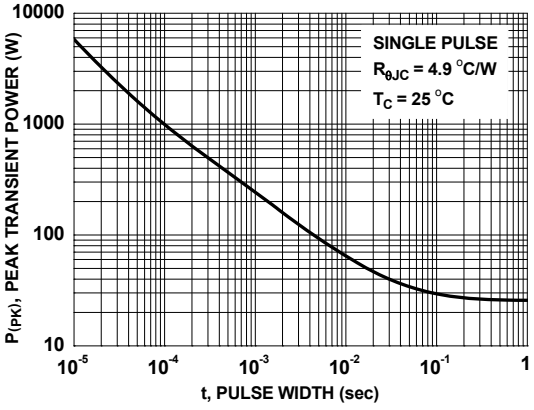


Figure 25. Single Pulse Maximum Power Dissipation

Typical Characteristics (Q2 N-Channel) T_J = 25 °C unless otherwise noted.

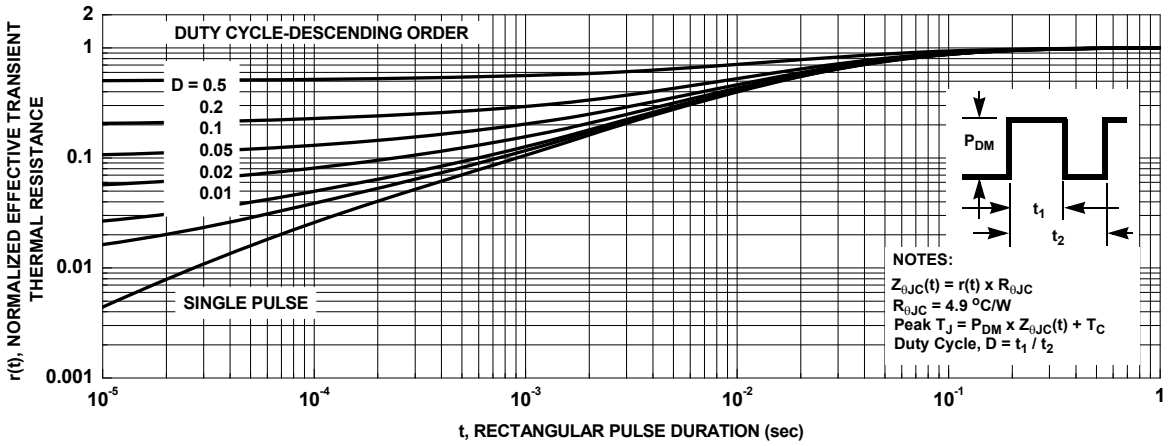


Figure 26. Junction-to-Case Transient Thermal Response Curve

Typical Characteristics (continued)

SyncFET™ Schottky Body Diode Characteristics

Fairchild's SyncFET™ process embeds a Schottky diode in parallel with PowerTrench® MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverse recovery characteristic of the FDPC5030SG.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

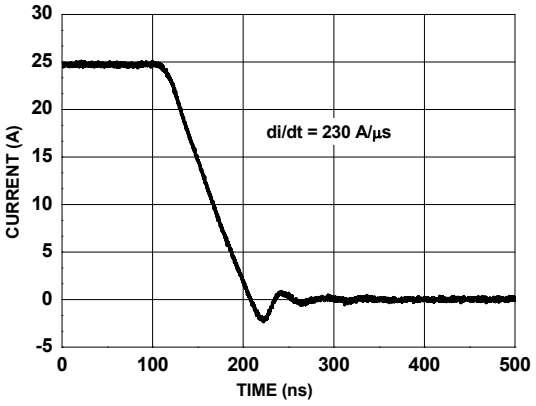


Figure 27. FDPC5030SG SyncFET™ Body Diode Reverse Recovery Characteristic

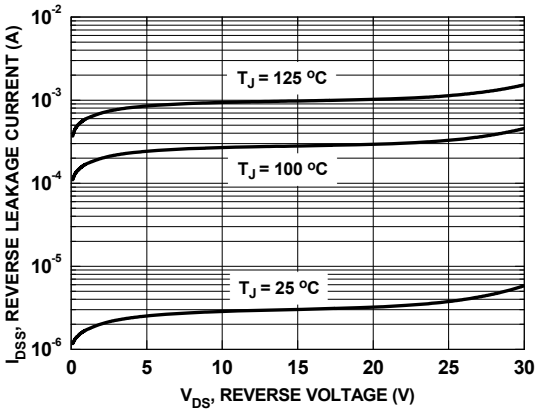
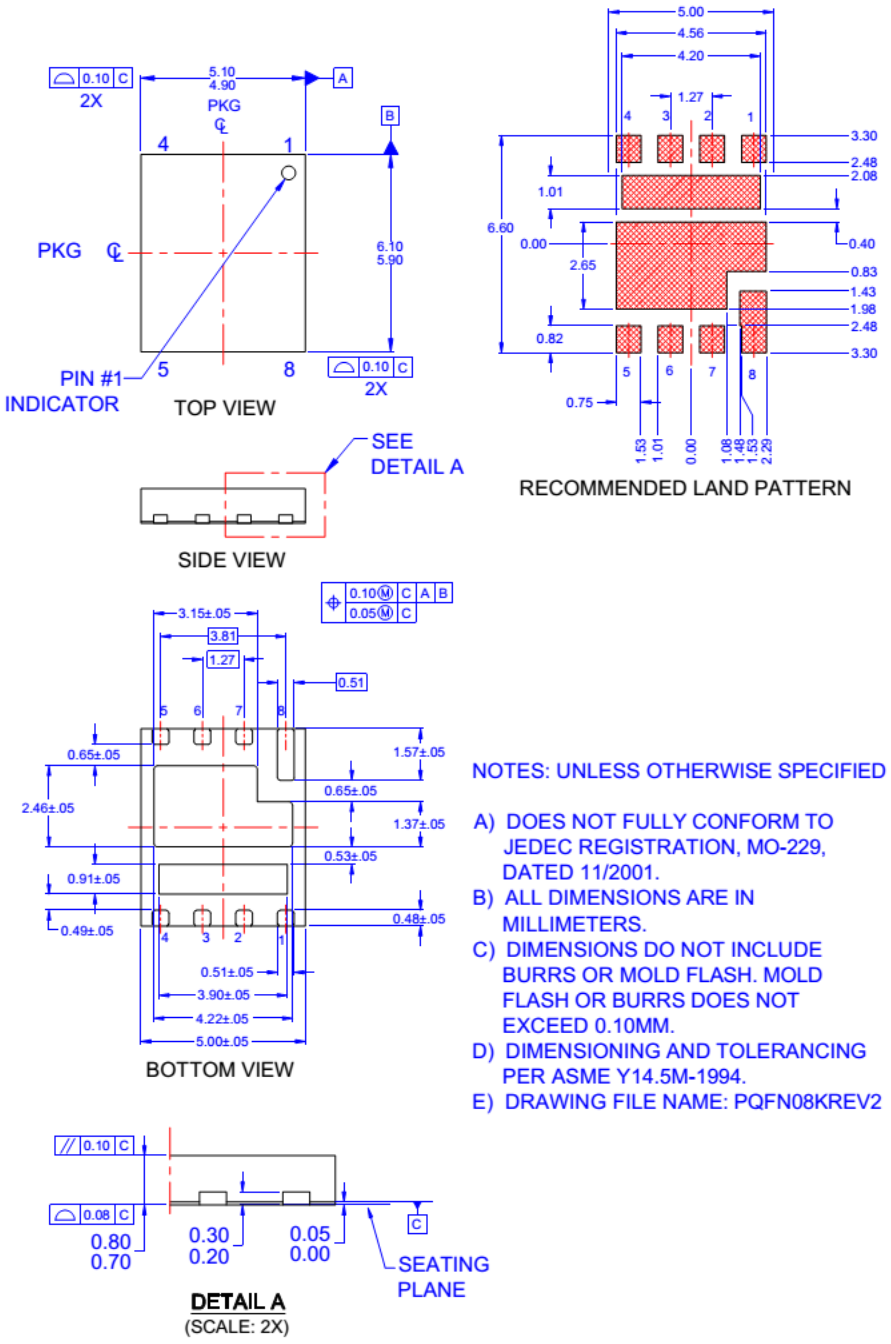


Figure 28. SyncFET™ Body Diode Reverse Leakage vs. Drain-Source Voltage

Dimensional Outline and Pad Layout



NOTES: UNLESS OTHERWISE SPECIFIED

A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
E) DRAWING FILE NAME: PQFN08KREV2

Package drawings are provided as a service to customers considering Fairchild components. Drawings may change in any manner without notice. Please note the revision and/or date on the drawing and contact a Fairchild Semiconductor representative to verify or obtain the most recent revision. Package specifications do not expand the terms of Fairchild's worldwide terms and conditions, specifically the warranty therein, which covers Fairchild products.

FAIRCHILD™

TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™
AttitudeEngine™
Awinda®
AX-CAP®*
BitSiC™
Build it Now™
CorePLUS™
CorePOWER™
CROSSVOLT™
CTL™
Current Transfer Logic™
DEUXPEED®
Dual Cool™
EcoSPARK®
EfficentMax™
ESBC™
Fairchild®
Fairchild Semiconductor®
FACT Quiet Series™
FACT®
FAST®
FastvCore™
FETBench™
FPS™
F-PFS™
FRFET®
Global Power Resource℠
GreenBridge™
Green FPS™
Green FPS™ e-Series™
G*max*™
GTO™
IntelliMAX™
ISOPLANAR™
Marking Small Speakers Sound Louder and Better™
MegaBuck™
MICROCOUPLER™
MicroFET™
MicroPak™
MicroPak2™
MillerDrive™
MotionMax™
MotionGrid®
MTi®
MTx®
MVN®
mWSaver®
OptoHiT™
OPTOLOGIC®
OPTOPLANAR®
Power Supply WebDesigner™
PowerTrench®
PowerXS™
Programmable Active Droop™
QFET®
QS™
Quiet Series™
RapidConfigure™
Saving our world, 1mW/W/kW at a time™
SignalWise™
SmartMax™
SMART START™
Solutions for Your Success™
SPM®
STEALTH™
SuperFET®
SuperSOT™-3
SuperSOT™-6
SuperSOT™-8
SupreMOS®
SyncFET™
Sync-Lock™
SYSTEM GENERAL®*
TinyBoost®
TinyBuck®
TinyCalc™
TinyLogic®
TINYOPTO™
TinyPower™
TinyPWM™
TinyWire™
TranSiC™
TriFault Detect™
TRUECURRENT®*
μSerDes™
UHC®
Ultra FRFET™
UniFET™
VCX™
VisualMax™
VoltagePlus™
XS™
Xsens™
仙童™

*Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT HTTP://WWW.FAIRCHILDSEMI.COM. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used here in:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I74

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative